CSD17301Q5

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N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ.)
30	0.0018 at V_{GS} = 10 V	100	82 nC
	0.0025 at V_{GS} = 4.5 V	90	

FEATURES

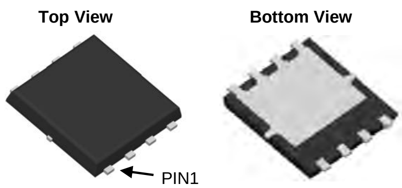
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

RoHS
COMPLIANT

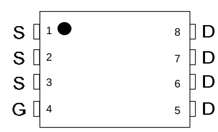
APPLICATIONS

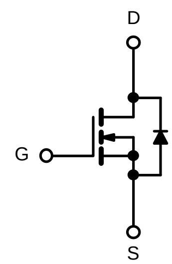
- OR-ing
- Server

DFN5X6



Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	100[a, e]	A
	T_C = 70 °C		90[e]	
	T_A = 25 °C		33[b, c]	
	T_A = 70 °C		29.8[b, c]	
Pulsed Drain Current		I_{DM}	300	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	36	
Single Pulse Avalanche Energy		E_{AS}	64.8	mJ
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	90[a, e]	A
	T_A = 25 °C		3.13[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	250[a]	W
	T_C = 70 °C		175	
	T_A = 25 °C		3.75[b, c]	
	T_A = 70 °C		2.63[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	

Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

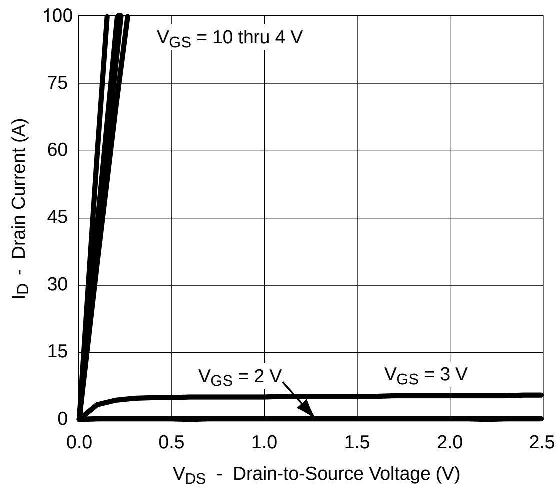
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	90			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 32 A		0.0018		Ω
		V_{GS} = 4.5 V, I_D = 29 A		0.0025		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 32 A		160		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS}= 12.5 V, V_{GS} = 0 V, f = 1 MHz		2765		pF
Output Capacitance	C_{oss}			1725		
Reverse Transfer Capacitance	C_{rss}			970		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 32 A		171	257	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 29 A		81.5	123	
Gate-Source Charge	Q_{gs}			34		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.555 Ω $I_D \cong$ 27 A, V_{GEN} = 10 V, R_g = 1 Ω		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.625 Ω $I_D \cong$ 24 A, V_{GEN} = 4.5 V, R_g = 1 Ω		55	83	
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			100	A
Pulse Diode Forward Current[a]	I_{SM}				200	
Body Diode Voltage	V_{SD}	I_S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/µs, T_J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

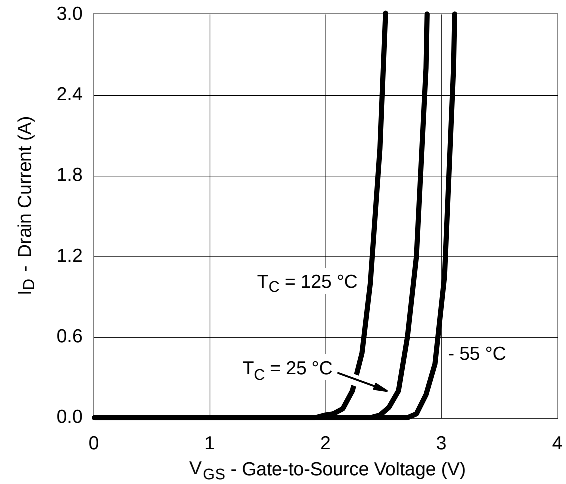
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

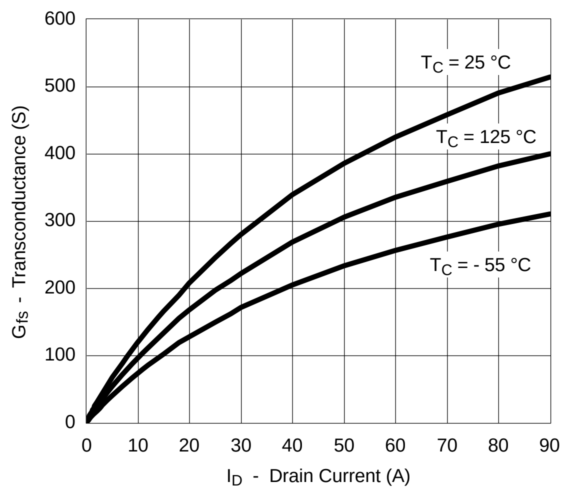
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



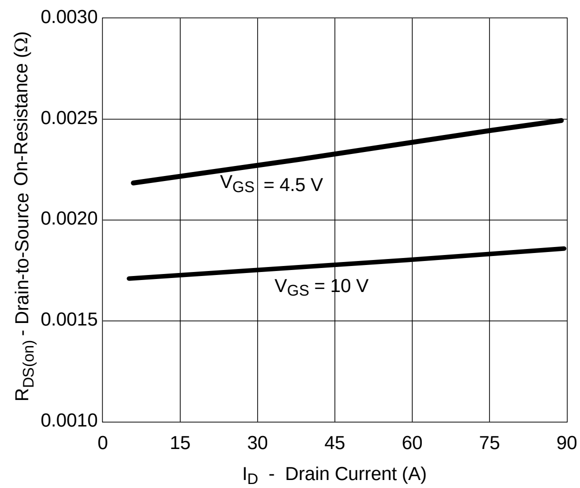
Output Characteristics



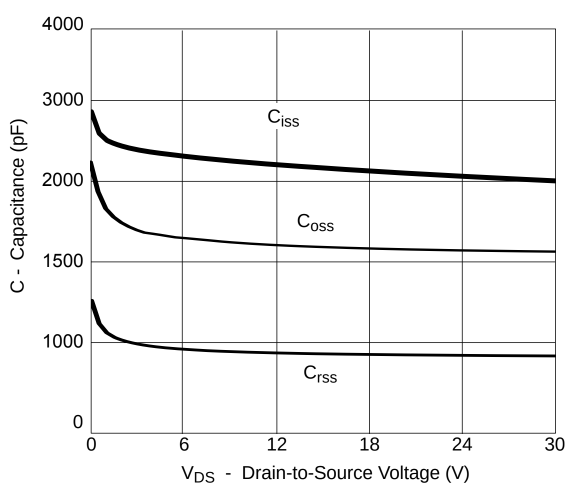
Transfer Characteristics



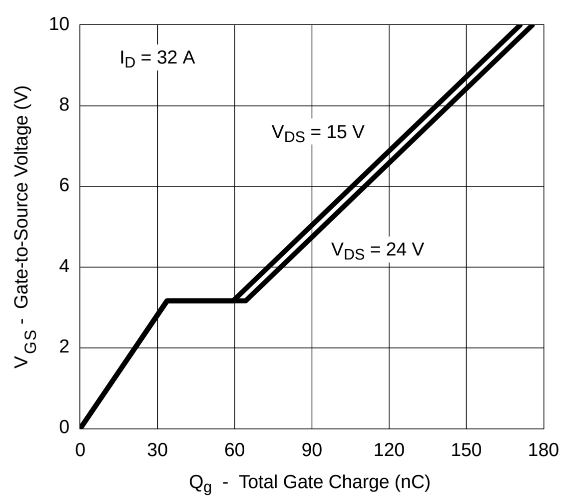
Transconductance



$R_{DS(on)}$ vs. Drain Current

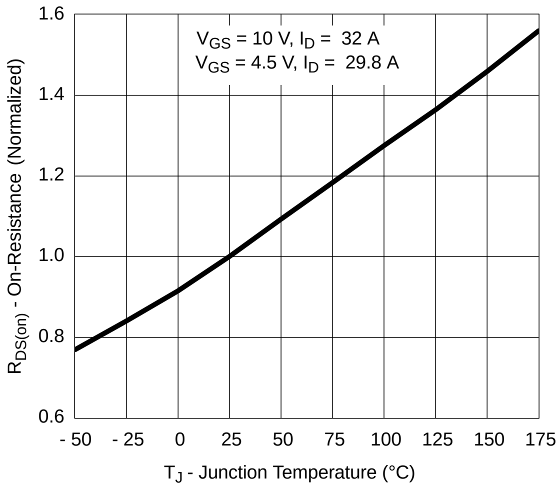


Capacitance

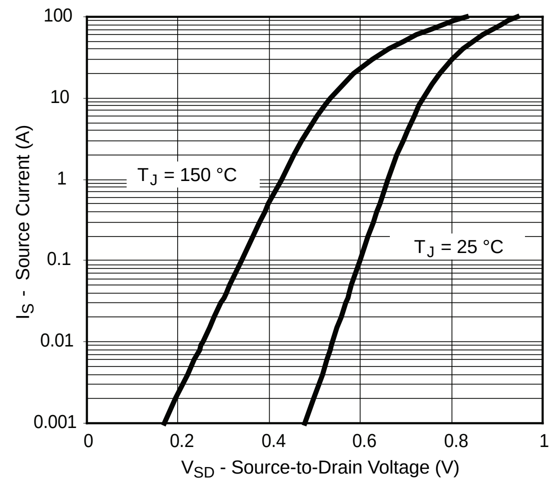


Gate Charge

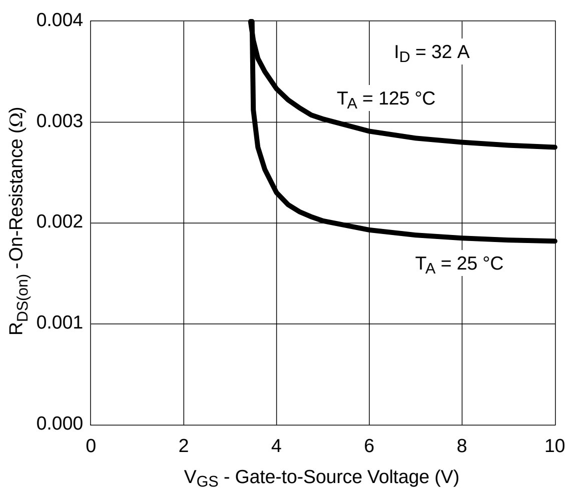
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



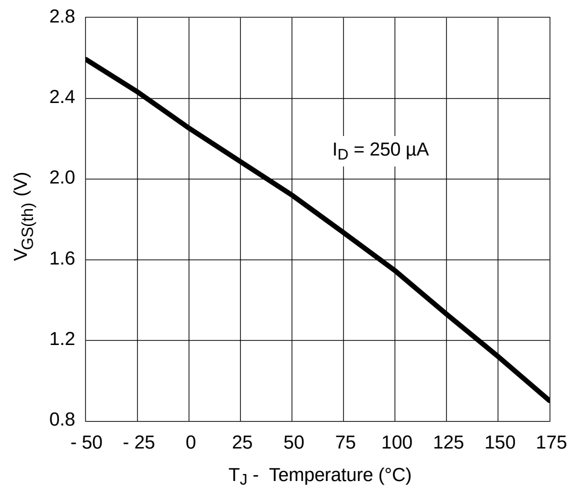
On-Resistance vs. Junction Temperature



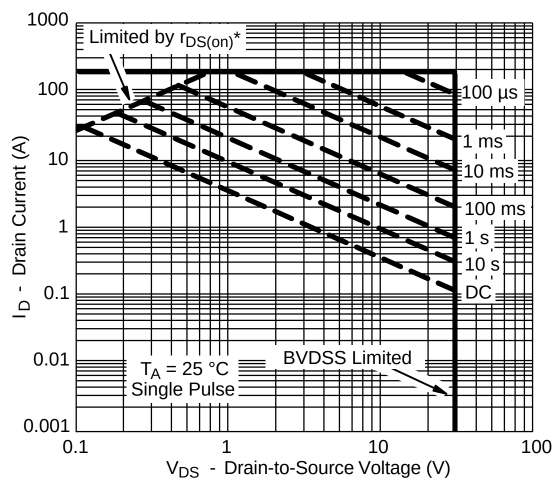
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature



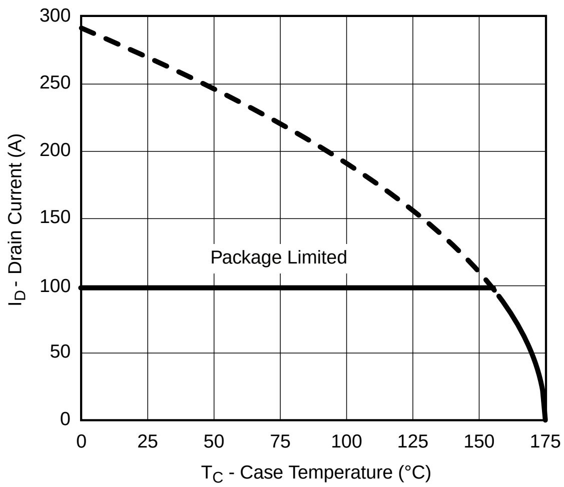
Threshold Voltage



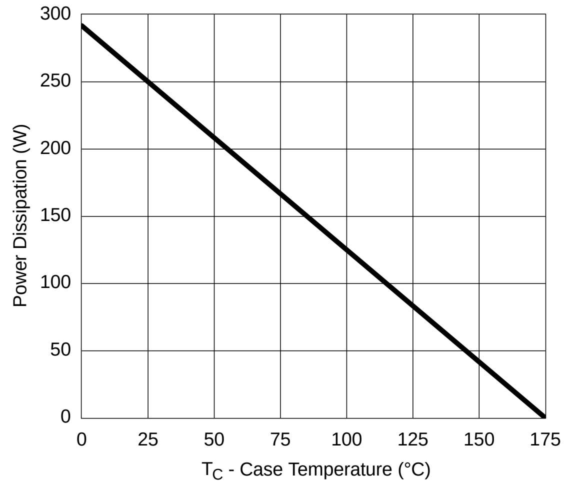
*V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

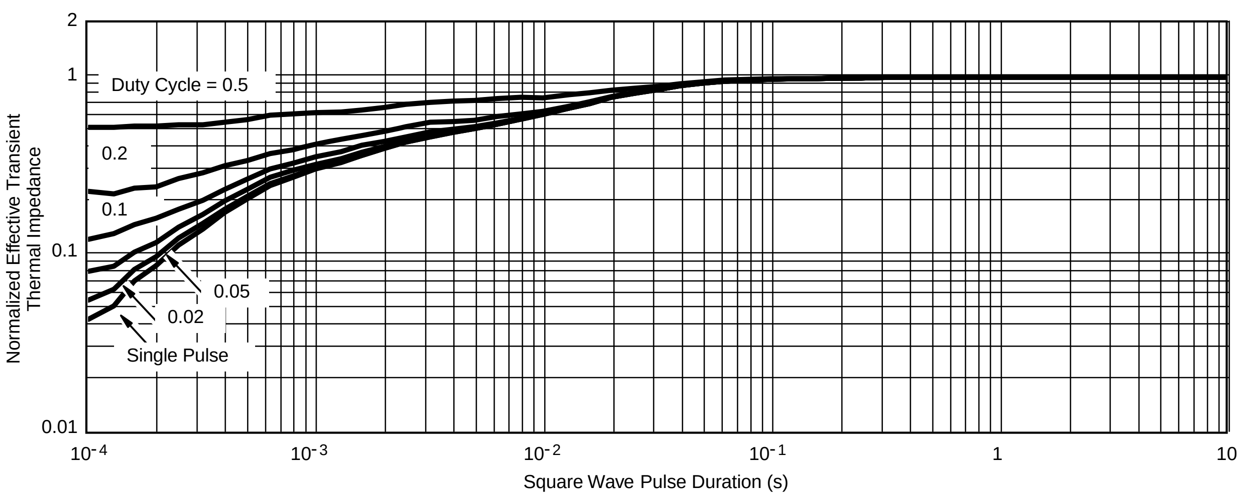


Current Derating*



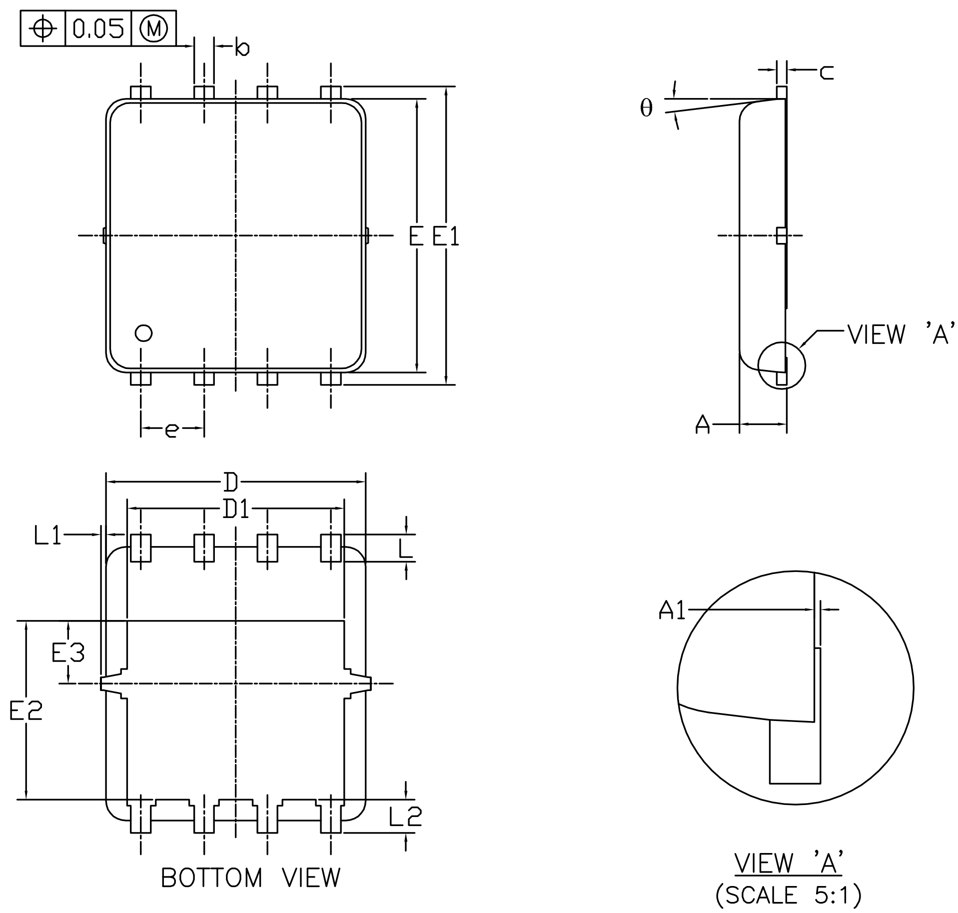
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

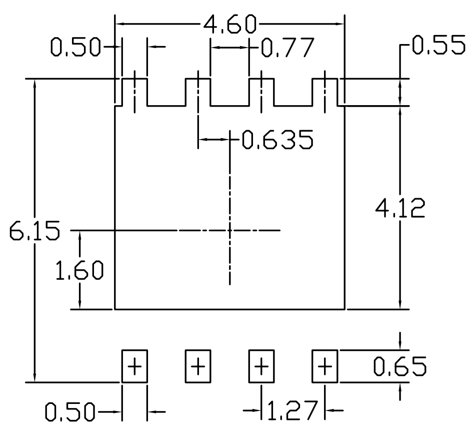


Normalized Thermal Transient Impedance, Junction-to-Case

DFN5x6_8L_EP1_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
   CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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